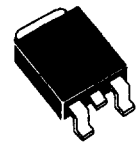
CJD2955 PNP
CJD3055 NPN

COMPLEMENTARY SILICON POWER TRANSISTOR

Central™ Semiconductor Corp.



DPAK CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD2955, CJD3055 types are Complementary Silicon Power Transistors manufactured by the epitaxial base process, mounted in a surface mount package designed for high current amplifier and switching applications.

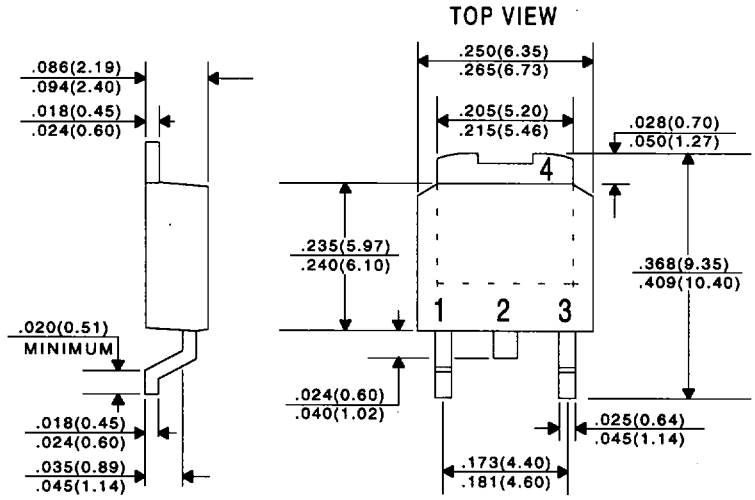
MAXIMUM RATINGS (T_C=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	70	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	10	A
Base Current	I_B	6.0	A
Power Dissipation (T_C=25°C)	P_D	20	W
Power Dissipation (T_A=25°C)	P_D	1.75	W
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JC}	6.25	°C/W
Thermal Resistance	Θ_{JA}	71.4	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEO}	V_{CE}=30V		50	μA
I_{CEV}	V_{CE}=70V, $V_{BE(off)}$=1.5V		20	μA
I_{CEV}	V_{CE}=70V, $V_{BE(off)}$=1.5V, T_C=150°C		2.0	mA
I_{CBO}	V_{CB}=70V		20	μA
I_{CBO}	V_{CB}=70V, T_C=150°C		2.0	mA
I_{EBO}	V_{EB}=5.0V		500	μA
BV_{CEO}	I_C=30mA	60		V
$V_{CE(SAT)}$	I_C=4.0A, I_B=400mA		1.1	V
$V_{CE(SAT)}$	I_C=10A, I_B=3.3A		8.0	V
$V_{BE(ON)}$	V_{CE}=4.0V, I_C=4.0A		1.8	V
h_{FE}	V_{CE}=4.0V, I_C=4.0A	20	100	
h_{FE}	V_{CE}=4.0V, I_C=10A	5.0		
f_T	V_{CE}=10V, I_C=500mA, f=1.0MHz	2.0		MHz

All dimensions in inches (mm).



LEAD CODE:

1) BASE
2) COLLECTOR
3) EMITTER
4) COLLECTOR

DATA SHEET

R2